



FINAL
Examination Paper
(COVER PAGE)

Session : April 2016

Programme : Diploma in Electrical and Electronic Engineering (DEEI)

Course : **EGM 1182: Structures and Properties of Material**

Date of Examination : 26 July 2016, Tuesday 2016

Time : 5.00pm – 7.00pm

Duration : 2 Hours Reading Time : Nil

Special Instructions :

This paper consists of **SIX (6)** questions. Answer any **FOUR (4)** questions in the answer booklet provided. All questions carry equal marks.

IMPORTANT NOTE : THIS PAPER SHOULD NOT BE TAKEN OUT OF THE EXAMINATION HALL

Materials Permitted : Nil

Materials Provided : Answer Booklet

Examiner(s) : **Mr. Phua Chin Lai**

Moderator : Prof. Ir. Dr. Cheong Kuan Yew

This paper consists of 7 printed pages, including the cover page.

INTI INTERNATIONAL COLLEGE

DIPLOMA IN ELECTRICAL AND ELECTRONIC ENGINEERING (DEEI)
EGM 1182: STRUCTURES AND PROPERTIES OF MATERIAL
FINAL EXAMINATION: APRIL 2016 SESSION

Instructions: This paper consists of **SIX (6)** questions. Answer any **FOUR (4)** questions in the answer booklet provided. All questions carry equal marks.

Question 1

(a) Briefly describe the following material:

- (i) Crystalline material
- (ii) Single crystal material
- (iii) Polycrystalline material.

(5 marks)

(b) Write the electron configurations of the following ion by using *spdf* notation:

- (i) Cr^{2+} ,
- (ii) Br^{-} .

(6 marks)

(c) An optical fiber for telecommunication is made of SiO_2 glass (density = 2.20 Mg/m^3). How many Si atoms and O atoms are present per millimeter of length of a fiber with diameter of $10 \mu\text{m}$? (Given $N_A = 6.023 \times 10^{23}$)

(8 marks)

(d) Calculate the ionic packing factor (or atomic packing factor) of CaO, which shares the NaCl type structure. Given the radius of Ca^{2+} is 0.106 nm and the radius of O^{2-} is 0.132 nm .

(6 marks)

Question 2

(a) Calculate the density of zinc blende (with tetrahedral structure) in term of g/cm^3 . Given the radius of Zn^{2+} is 0.083 nm and the radius of S^{2-} is 0.174 nm .

(6 marks)

(b) To produce a p-type of semiconductor, small level of impurities (aluminium) are added to an essentially pure semiconductor (silicon) in order to produce desirable electrical properties. For 5×10^{21} aluminium atoms per cubic meter in solid solution of silicon, calculate

- (i) the atomic percent of aluminium atoms. Given the density of silicon as 2.33 Mg/m^3 .
- (ii) the weight percent of aluminium atoms.

(11 marks)

- (c) Calculate the center to center separation distance (or lattice constant) of two Fe atoms along the [1 0 0] direction in unstressed α - iron. Given the radius of iron atom is 0.124nm.
 Subsequently determine the separation distance of two atoms along the same direction under a tensile stress of 1000 MPa. Given the modulus of elasticity of α - iron as 125 GPa.

(8 marks)

Question 3

- (a) Given the Al - Si phase diagram in Figure 3. Calculate
 (i) The weight fraction of the α phase that is proeutectic in a 10 wt% Si - 90 wt% Al alloy at 576 °C, and
 (ii) The weight fraction of the β phase that is proeutectic in 20 wt% Si - 80 wt% Al alloy at 576 °C.

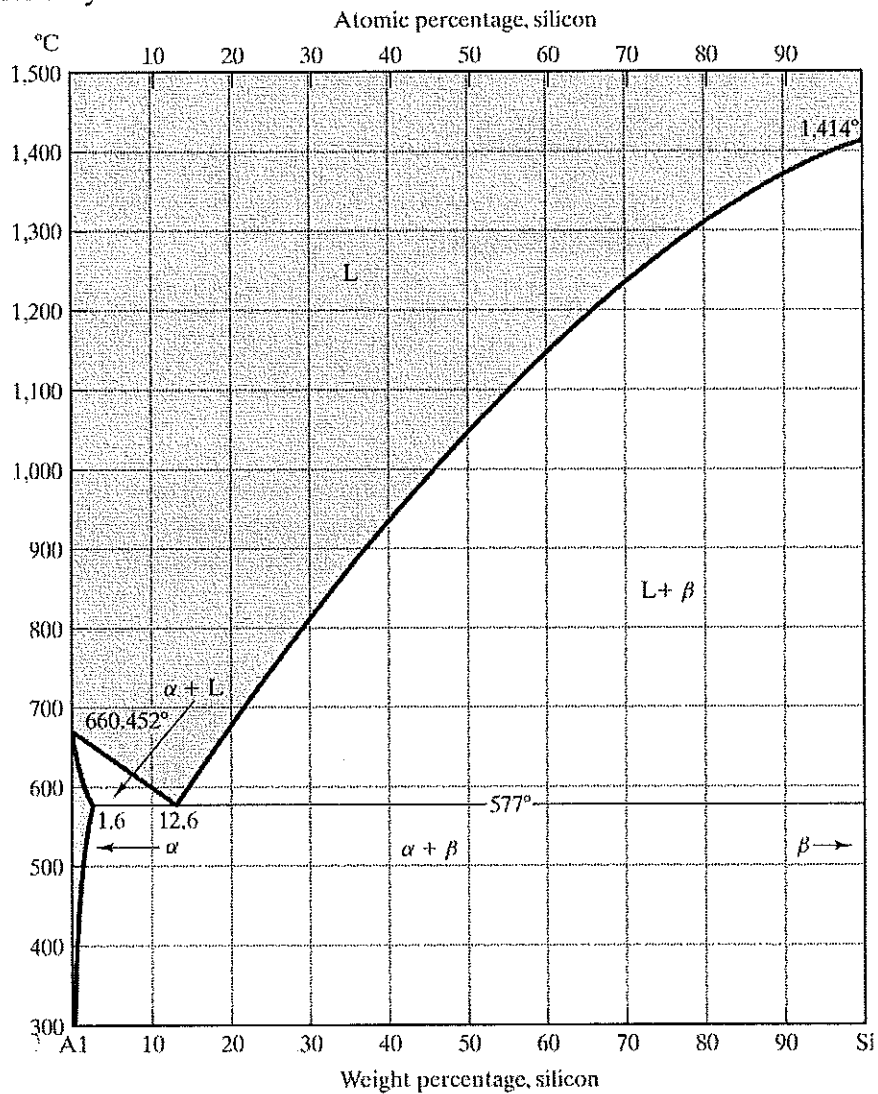


Figure 3

(10 marks)

(b) Calculate the atomic packing factor for polyethylene $-\text{[C}_2\text{-H}_4\text{]}_n-$. If the unit cell volume is 0.0933 nm^3 , the radius of carbon and hydrogen are 0.077 nm and 0.046 nm respectively. Each unit cell would contain 2 repeating unit of monomer.

(7 marks)

(c) Define the following terms related to the mechanical behavior of materials

- (i) Endurance limits,
- (ii) Fatigue strength,
- (iii) Engineering stress and its SI unit,
- (iv) Engineering strain and its SI unit.

(8 marks)

Question 4

(a) A cylindrical specimen of steel having an original diameter of 12.8 mm is tensile tested to fracture and found to have an engineering fracture strength of 460 MPa . If its cross sectional is 10.7 mm , determine:

(i) The engineering stress and true stress

(5 marks)

(i) The engineering strain and true strain

(5 marks)

(b) Define or briefly explain the following:

(i) Annealing of steels

(4 marks)

(ii) Tempering of steels

(4 marks)

(c) A steel bar 100 mm long and having a square cross section $20 \text{ mm} \times 20 \text{ mm}$ is pulled in tension with a force of $8.9 \times 10^4 \text{ N}$, and experiences an elongation of 0.1 mm . Assuming that the deformation is entirely elastic, calculate the modulus of elasticity of the steel.

(7 marks)

Question 5

(a) Distinguish between traditional ceramic and engineering ceramic materials and for each type of ceramic, gives TWO (2) examples.

(6 marks)

(b) For a ceramic compound, what are the two characteristics of the component ions that determine the crystal structure?

(4marks)

(c) Refer to Figure 5. Define the following phases that exist in the Fe-Fe₃C phase diagram:

- (i) austenite,
- (ii) α ferrite,
- (iii) cementite,
- (iv) δ ferrite.

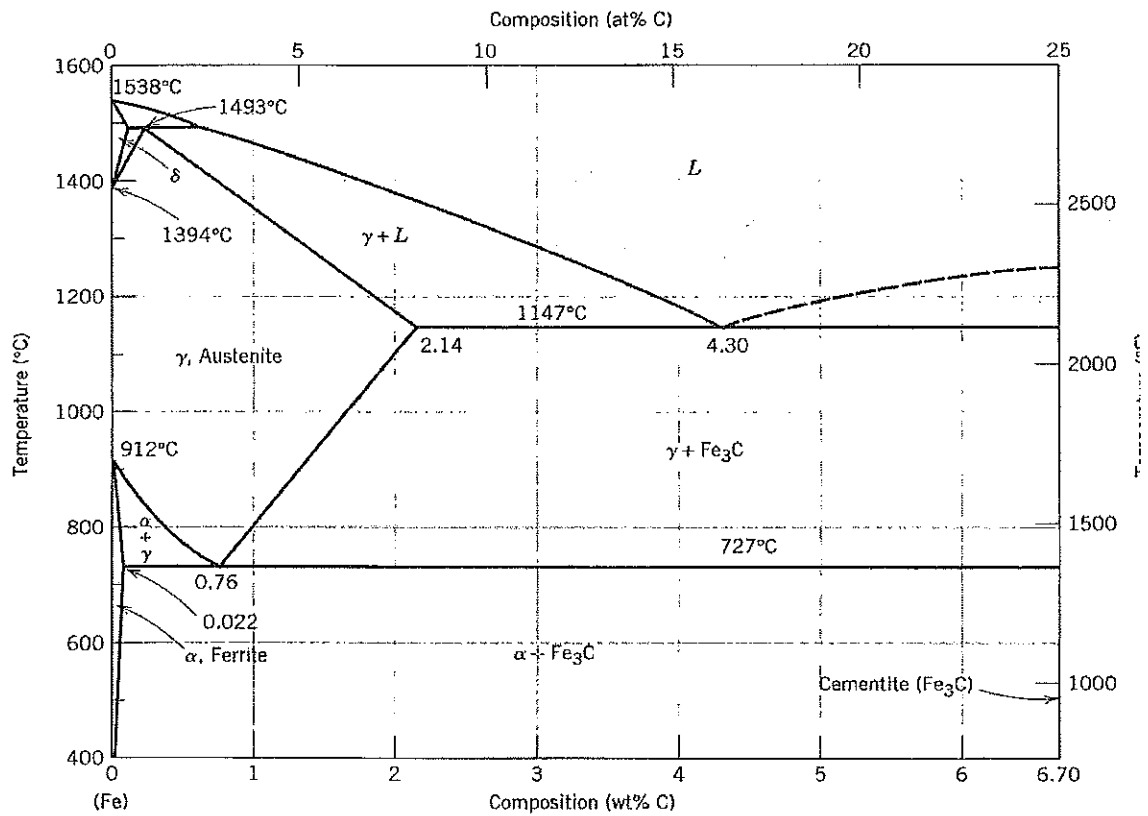


Figure 5

(10 marks)

(d) Write Ohm's law equation for microscopic form. Define the symbols and indicate their SI units.

(5 marks)

Question 6

(a) Define the following terms:

- (i) electrical conductivity
- (ii) n-type extrinsic semiconductor
- (iii) electron drift velocity
- (iv) band gap

(8 marks)

(b) Calculate the electrical conductivity of pure copper at:

- (i) 400°C
- (ii) -100°C

Comment on your results obtained in terms of the effect of temperature on conductivity of copper with the given resistivity of copper at 0°C is $1.67 \times 10^{-6} \Omega \cdot \text{cm}$ and its temperature resistivity coefficient is $0.0068/^{\circ}\text{C}$.

(7 marks)

(c) Determine the Miller indices for the A, B and C plane shown in the following unit cell (Figure 6).

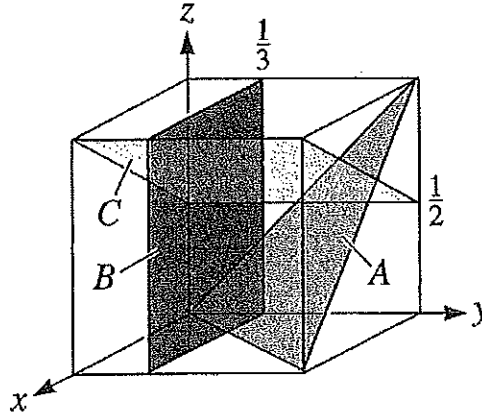


Figure 6

(6 marks)

(d) What type(s) of bonding would be expected for each of the following materials:

- (i) brass (copper-zinc alloy),
- (ii) rubber,
- (iii) barium sulfide (BaS),
- (iii) solid xenon.

(4 marks)

-THE END-

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APPENDIX I

PERIODIC TABLE

KEY		Atomic Number	Symbol of Element	Name of Element
1	H	1	H	Hydrogen
2	He	2	He	Helium
3	Li	3	Li	Lithium
4	Be	4	Be	Beryllium
5	B	5	B	Boron
6	C	6	C	Carbon
7	N	7	N	Nitrogen
8	O	8	O	Oxygen
9	F	9	F	Fluorine
10	Ne	10	Ne	Neon
11	Na	11	Na	Sodium
12	Mg	12	Mg	Magnesium
13	Al	13	Al	Aluminium
14	Si	14	Si	Silicon
15	P	15	P	Phosphorus
16	S	16	S	Sulfur
17	Cl	17	Cl	Chlorine
18	Ar	18	Ar	Argon
19	K	19	K	Potassium
20	Ca	20	Ca	Calcium
21	Sc	21	Sc	Scandium
22	Ti	22	Ti	Titanium
23	V	23	V	Vanadium
24	Cr	24	Cr	Chromium
25	Mn	25	Mn	Manganese
26	Fe	26	Fe	Iron
27	Co	27	Co	Cobalt
28	Ni	28	Ni	Nickel
29	Cu	29	Cu	Copper
30	Zn	30	Zn	Zinc
31	Ga	31	Ga	Gallium
32	Ge	32	Ge	Germanium
33	As	33	As	Arsenic
34	Se	34	Se	Selenium
35	Br	35	Br	Bromine
36	Kr	36	Kr	Krypton
37	Rb	37	Rb	Rubidium
38	Sr	38	Sr	Strontium
39	Y	39	Y	Yttrium
40	Zr	40	Zr	Zirconium
41	Nb	41	Nb	Niobium
42	Mo	42	Mo	Molybdenum
43	Tc	43	Tc	Technetium
44	Ru	44	Ru	Ruthenium
45	Rh	45	Rh	Rhodium
46	Pd	46	Pd	Palladium
47	Ag	47	Ag	Silver
48	Cd	48	Cd	Cadmium
49	In	49	In	Indium
50	Sn	50	Sn	Tin
51	Sb	51	Sb	Antimony
52	Te	52	Te	Tellurium
53	I	53	I	Iodine
54	Xe	54	Xe	Xenon
55	Cs	55	Cs	Cesium
56	Ba	56	Ba	Barium
57	La	57	La	Lanthanum
58	Ce	58	Ce	Cerium
59	Pr	59	Pr	Praseodymium
60	Nd	60	Nd	Neodymium
61	Pm	61	Pm	Promethium
62	Sm	62	Sm	Samarium
63	Eu	63	Eu	Europium
64	Gd	64	Gd	Gadolinium
65	Tb	65	Tb	Terbium
66	Dy	66	Dy	Dysprosium
67	Ho	67	Ho	Holmium
68	Er	68	Er	Erbium
69	Tm	69	Tm	Thulium
70	Yb	70	Yb	Ytterbium
71	Lu	71	Lu	Lutetium
72	Hf	72	Hf	Hafnium
73	Ta	73	Ta	Tantalum
74	W	74	W	Tungsten
75	Re	75	Re	Rhenium
76	Os	76	Os	Osmium
77	Ir	77	Ir	Iridium
78	Pt	78	Pt	Platinum
79	Au	79	Au	Gold
80	Hg	80	Hg	Mercury
81	Tl	81	Tl	Thallium
82	Pb	82	Pb	Lead
83	Bi	83	Bi	Bismuth
84	Po	84	Po	Polonium
85	At	85	At	Astatine
86	Rn	86	Rn	Radon
87	Fr	87	Fr	Francium
88	Ra	88	Ra	Radium
89	Ac	89	Ac	Actinium
90	Th	90	Th	Thorium
91	Pa	91	Pa	Protactinium
92	U	92	U	Uranium
93	Np	93	Np	Neptunium
94	Pu	94	Pu	Plutonium
95	Am	95	Am	Americium
96	Cm	96	Cm	Curium
97	Bk	97	Bk	Berkelium
98	Cf	98	Cf	Californium
99	Es	99	Es	Einsteinium
100	Fm	100	Fm	Fermium
101	Md	101	Md	Mendelevium
102	No	102	No	Nobelium
103	Lr	103	Lr	Lawrencium

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